TECHNICAL SPEC FOR Stepper

System Model: Canon FPA 3000 i4 SN 601596i4

Tool has been shut down by Litho tech. Electricity, cooling water, Vacuum and CCA are closed. Cables between Main unit and power box are still connected, locking kit and demounting for transport to be provided by buyer.

Wafer size: 6 inch

Wafer type: Jeida flat

Chuck type: 8 inch, pin chuck

Reticle changer type: (Canon standard?) I4 library Canon

Inline right or left: left

Particle checker (PPC): No

Touch panel type: Canon standard

Options:

Reticle size: 5 inch

Reticle alignment: see specs below

Wafer alignment: see specs below

Auto focus:see specs below

Auto feeder: Yes

Wafer tilt:

Wafer feeder: Yes

Track interface: Yes, tool was used inline, interface is track part

Laser: HeNe

Lens data: see below

Stage and U-lens at shutdown Intensity: 400 mW/cm2 Uniformity: 2.8%

Stage vibration data:

Used for 0.35micron line and space? Y

Chuck maintenance tool: No

Reticle bar code reader: Yes

Cassette bar code reader: No

SW Version:

OS:

Vintage: 2006

Missing/defective parts: none

| ACCEPTANCE CANON STEPPER 8 300014 | | | SPECIFICATION | RESULT | JUDGE |
|-----------------------------------|----------------|---|------------------------|-------------------------|-------|
| Juni 1997 | _ | | | | |
| 1. ILLUMINATOR | 18. | Intensity (Normal Illumination) | 2 650mW/cm2 | 903mW/cm2 | ð |
| | | Intensity (Off-Axis Illumination, Sia) | ≥ 400mW/cm2 | 527.5mW/cm2 | ¥ |
| | | Intensity (Off-Axis Illumination, Sib) | > 400mW/cm2 | 511.8mW/cm2 | ¥ |
| | 1b. | Illumination Uniformity (Normal Illumination) | < ±1% | 0.7% | ¥ |
| | | Illumination Uniformity (Off-Axis Illumination, Sia) | ≤ ±1.3% | 1.0% | ð |
| | | Illumination Uniformity (Off-Axis Illumination, Sib) | ≤ ±1.3% | 1.0% | ¥ |
| | 1 ⁰ | Dose Control Accuracy | < ±1% | 0.31% | ¥ |
| | 1d. | Dose Repeatability CD Method (28 days) 0.35 ± 0.035µ | Cp ≥ 1.0 | 1.17 | ş |
| | | Dose Repeatability CD Method (28 days) 0.50 ± 0.050 µ | Cp ≥ 1.3 | 1.4 | ¥ |
| | 1e. | Dose Matching Between Steppers CD Method 0.35µ | ≤ ± 0.015µ | 0.015 (st5) 0.012 (st6) | ð |
| | | Dose Matching Between Steppers CD Method 0.50µ | ≤ ± 0.015µ | 0.0067 µ | ş |
| | | Masking Blade Accuracy (Wafer level) | 5 ± 100 µ | 60µ | ð |
| | 1g. | Reticle Change Time (Including Alignment) | < 60 secs | 57 secs | ð |
| 2. EXPOSURE PERFORMANCE | 2a. | . CD 0.35µ DOF (+/- 10%) | ≥ 0.6µ | 1μ | ð |
| | | Slope 0.35µ DOF (>82degr) | ≥ 0.6µ | 0.7µ | ð |
| | _ | overlapping UDOF 0.35µ | ≥ 0.6µ | 0.7µ | ð |
| | | Linearity 0.35µ | < 10% | 4.10% | ¥ |
| | _ | Proximity Effect 0.35µ | < 0.05µ | 0.0489µ | ð |
| | 2b. | CD 0.32µ DOF (+/- 10%) | ≥ 0.8µ | 1.0µ | ð |
| | | Slope 0.32µ (>82.6 degr) | ≥ 0.8µ | 0.9µ | ð |
| | | overlapping UDOF 0.32µ | ≥ 0.8µ | 0.9µ | ð |
| | | Linearity 0.32µ | ≤ 10% | 7.50% | ð |
| | 2c. | CD 0.50µ DOF (+/- 10%) | ≥ 1.2µ | 1.5µ | ð |
| | | Stope 0.50µ DOF (>80degr) | ≥ 1.2µ | 1.6µ | ¥ |
| | | UDOF 0.50µ | ≥ 1.2µ | 1.5µ | ð |
| | _ | Linearity 0.50µ (9H,9V at best focus van 0.5-1µ, incr. 0.05µ) | < 10% | 8.90% | ð |
| | | Proximity Effect 0.50µ (9H,9V at best focus) | ≤ 0.05µ | .02µ | ð |
| | _ | Assymmetry 0.50µ (9H,9V at -0.75mm focus) | < 5gr | 1.9degr | ð |
| | 2d. | Linewidth Repeatability Within Field 0.35µ lines | $0.35\mu \pm 0.02\mu$ | 0.0306µ | ð |
| | | Linewidth Repeatability Within Field 0.35 µ slopes | ≥ 85gr | 83.1gr | ę, |
| | | Linewidth Repeatability Within Field 0.5 lines | $0.50\mu \pm 0.025\mu$ | 0.66µ | ok. |
| | | Linewidth Repeatability Within Field 0.5µ slopes | 2 85gr | 85.6degr | ok, |
| | 2e. | Linewidth Repeatability Within Wafer 0.35 µ lines | $0.35\mu \pm 0.02\mu$ | 0.0156µ | ¥ |
| | _ | Linewidth Repeatability Within Wafer 0.35µ slopes | ≥ 85gr | 83.7gr | ok, |
| | | Linewidth Repeatability Within Wafer 0.50µ lines | 0.50µ ± 0.025µ | 0.66 µ | ok. |
| | | Linewidth Repeatability Within Wafer 0.50µ slopes | ≥ 85gr | 85.6degr | •¥• |

| | | | - | |
|------------------|--------------------------------------|---|--|--|
| | | ≤ ± 0.05μ | s ± 0.06 μ | ≤ ± 0.06µ |
| | | | + | |
| | IETEC | llumination) | SIA) | SiB) |
| 0004 | CATEL-M | (Normal 1 | (Off-axis | (Off-axis |
| PA 30 | RAL | Grid | Grid | Grid |
| CANON FPA 3000i4 | coeptance results FOR ALCATEL-MIETEC | From Ideal Cartesian Grid (Normal Illuminatic | From Ideal Cartesian Grid (Off-axis SiA) | From Ideal Cartesian Grid (Off-axis SiB) |
| Ī | tance | Ideal | deal | Ideal |
| | Accep | From | From | From |

| | 21. | Distortion - Deviation From Ideal Cartesian Grid (Normal Illumination) | < ± 0.05µ | 0.014µ (X): 0.023 µ (Y) | ð |
|----------------------------|-----|--|------------------|------------------------------|---|
| | | Distortion - Deviation From Ideal Cartesian Grid (Off-axis SiA) | vı | 0.012µ (X); 0.023 µ (Y) | ð |
| | | Distortion - Deviation From Ideal Cartesian Grid (Off-axis SiB) | < ± 0.06µ | 0.014µ (X); 0.027 µ (Y) | ¥ |
| | | Distortion Matching - Stepper8 to Mietec Reference Wafer | VI | 0.037 µ (X); 0.024 µ (Y) | ¥ |
| | | Distortion Matching - Stepper8 to Stepper6 | VI | 0.015µ (X); 0.062 µ (Y) | ¥ |
| | | Distortion Matching - Stepper8 to Stepper5 | | 0.009 µ (X); 0.018 µ (Y) | ð |
| | | Distortion Matching - Stepper8 to Stepper4 | ≤ ± 0.08µ | 0.077 µ (X); 0.057 µ (Y) | ş |
| | | Distortion Matching - Stepper8 to Stepper3 | VI | 0.034 µ (X); 0.046 µ (Y) | ¥ |
| | | Distortion Matching - Stepper8 to Stepper2 | vi | 0.036 µ (X); 0.034 µ (Y) | ¥ |
| | | Distortion Matching - Stepper8 to Stepper1 | s ± 0.08µ | 0.051µ (X); 0.025 µ (Y) | ¥ |
| 3. AUTO FOCUS ACCURACY | 3a. | Stability Over 28 days, 0.5µ lines | ≤ 0.3µ range | 0.3µ | ð |
| | 3b. | Maximum Deviation of Best Focus between Bare Silicon. | | | |
| | | Nitride, Polysilicon and Metal Wafers, 0.8µ lines | ≤ 0.3µ range | 0.075µ range | ð |
| | 3c. | Global Levelling Tilt | ≤ 7ppm 3sd | ≤ 1.96ppm (X) 1.56 (Y) 3sd | ð |
| | 3d. | Die by Die Levelling Stability Focus | ≤ 0.10µ 3sd | 0.019µ | ð |
| | 3e. | Die By Die Levelling Repeatability Tilt | ≤ 7ppm 3sd | 5.05ppm (X); 3.79ppm (Y) | ð |
| 4. AUTO ALIGNMENT ACCURACY | 4a. | Reticle Rotation Accuracy | ≤ ± 0.02µ | ≤ ± 0.00446μ | ð |
| HeNe and Broadband | | Reticle Rotation Repeatability | ≤ 0.03µ range | < 0.0074µ range | ¥ |
| | 4b. | AGA Accuracy Single Machine (Resist to Resist, Mode 1, Day1) | ≤ 0.06µ mean+3sd | 0.0368µ (YI); 0.0478µ (Yr) | ¥ |
| | | | | 0.0205µ (XI+Xr/2) | ¥ |
| | | AGA Accuracy Single Machine (Resist to Resist, Mode 1, Day2) | ≤ 0.06µ mean+3sd | 0.0495µ (YI); 0.0584µ (Yr) | ¥ |
| | | | | 0.0366µ (XI+Xr/2) | ş |
| | | AGA Accuracy Single Machine (Resist to Resist, Mode 1, Day3) | ≤ 0.06µ mean+3sd | 0.0364µ (YI); 0.0476µ (Yr) | ¥ |
| | | | | 0.0213µ (XI+Xr/2) | ¥ |
| | | AGA Accuracy Single Machine (Resist to Resist, Mode 4, Day1) | ≤ 0.06µ mean+3sd | 0.0386µ (X) | ð |
| | | | | 0.0530µ (Y) | ¥ |
| | | AGA Accuracy Single Machine (Resist to Resist, Mode 4, Day2) | ≤ 0.06µ mean+3sd | 0.0335µ (X) | ¥ |
| | | | | 0.0437µ (Y) | ¥ |
| | | AGA Accuracy Single Machine (Resist to Resist, Mode 4, Day3) | ≤ 0.06µ mean+3sd | 0.0281µ (X) | ¥ |
| | | | | 0.0432µ (Y) | ð |
| | 4c. | AGA Accuracy Machine to Machine | ≤ 0.09µ mean+3sd | 0.0846 µ (YI); 0.0890 µ (Yr) | ¥ |
| | | (Resist to Resist, stepper8-stepper6, Day 1) | | 0.0496µ (XI+Xr/2) | ð |
| | | AGA Accuracy Machine to Machine | ≤ 0.09µ mean+3sd | 0.0878 µ (YI); 0.0859 µ (Yr) | ð |
| | | (Resist to Resist, stepper8-stepper6, Day 2) | | 0.0437µ (XI+Xr/2) | ¥ |
| | | AGA Accuracy Machine to Machine | < 0.09µ mean+3sd | 0.0844 µ (YI); 0.0888 µ (Yr) | ¥ |
| | | (Resist to Resist, stepper8-stepper6, Day 3) | | 0.0498µ (XI+Xr/2) | ę |
| | 4d. | Overlay Guarantee ALL Process Layers and ALL Machines | ≤ 0.20µ X + 3sd | : | ¥ |
| | 4e. | Layer and Device Alignment Offsets | Fixed | Fixed | ð |

| 5 0.04µ 3sd 0.0117µ (X); 0.0125µ (Y) 5 0.04µ 3sd 0.0169µ (X); 0.0127µ (Y) 5 0.04µ 3sd 0.0169µ (X); 0.0209µ (Y) 5 0.04µ 3sd 0.0169µ (X); 0.0127µ (Y) 5 0.04µ 3sd 0.0169µ (X); 0.0127µ (Y) 5 ± 0.5pm 0.0169µ (X); 0.0232µ (Y) 5 ± 0.5pm 0.0169µ (X); 0.0232µ (Y) 5 ± 0.5pm 0.0151µ (X); 0.0232µ (Y) 6 fer Per Pass 5 10 aler Per Pass 5 10 and Develop Without 1.3.6 mm 2 for Pass 5 10 and Develop Without 2.5 2 for Pass 5 10 2 for Pass 2 1 2 for Pass 2 1 2 for Pass 2 1 2 for Pass 2 1 <th></th> <th></th> <th></th> <th></th> <th></th> <th></th> | | | | | | |
|--|---|----------------|---|-------------|----------------------------|--------|
| S 0.014µ 36d 0.0139µ (X0); 0.0221µ (Y1) S 0.0169µ (X0); 0.0127µ (Y1) 0.0106µ (X0); 0.0127µ (Y1) S 0.0169µ (X0); 0.0139µ (Y1); 0.0232µ (Y1) 0.0106µ (X1); 0.0232µ (Y1) S 2 0.0169µ (X1); 0.0232µ (Y1) S 2 0.0169µ (X1); 0.0232µ (Y1) S 2 0.015µ (X1); 5.0µ (Y1) afer Per Pass S 10 afer Per Pass S 0 afer Per Pass S 0 </th <th>5. X-Y STAGE</th> <th>5a.</th> <th>Stepping Accuracy Water 1</th> <th>≤ 0.04µ 3sd</th> <th>0.0117 (XI); 0.0125 (YI)</th> <th>¥</th> | 5. X-Y STAGE | 5a. | Stepping Accuracy Water 1 | ≤ 0.04µ 3sd | 0.0117 (XI); 0.0125 (YI) | ¥ |
| < 0.0108μ (XI); 0.0112/μ (YI) 5 0.04μ 3sd 0.0108μ (XI); 0.0114μ (YI) 5 0.04μ 3sd 0.0108μ (XI); 0.0114μ (YI) 5 ± 0.5ppm 0.0151μ (XI); 0.0114μ (YI) 5 ± 0.5ppm 0.0151μ (XI); 5.0μ (YI) 5 ± 0.5ppm 0.0151μ (XI); 5.0μ (YI) 5 ± 0.5ppm 0.044pm 5 ± 0.5ppm 0.044pm 5 ± 0.5ppm 0.044pm 6 ± 0.5ppm 0.0151μ (XI); 5.0μ (YI) 0 ± 6mm 1.3.76μ (XI); 5.0μ (YI) 0 ± 6mm 1.3.76μ (XI); 5.0μ (YI) 1 ± 3 ± 6 mm 1.1.3 ± 6 mm 40 ± 0.3/0.5 mm 1.1.3 ± 6 mm 1 ± 0.3/0.5 mm 1.1.3 ± 6 mm 1 ± 0.3/0.6 mm 1.1.3 ± 6 mm and Develop Without 2.5 2 ± 0 0 and Develop Without 2.5 2 ± 0 0 2 ± 0 0 2 ± 0 0 2 ± 0 0 2 ± 0 0 2 ± 0 0 2 ± 0 0 2 ± 0 0 | | | | | 0.0149µ (Xr); 0.0219µ (Yr) | ð |
| Image: Control of Contro of Contre of Contre of Contro of Contro of Contro of Contro of Contro o | | | Stepping Accuracy Wafer 2 | ≤ 0.04µ 3sd | 0.0108µ (XI); 0.0127µ (YI) | ¥ |
| ≤ 0.04µ 3sd 0.0103µ (Xi); 0.0114µ (Yi) ≤ ± 0.5pm ≤ ± 0.5pm ≤ ± 0.5pm ≤ ± 0.5pm ≤ ± 0.5pm ≤ 0.04pm ≤ ± 0.5pm ≤ 0.04pm ≤ ± 0.5pm -0.04pm 0.0151µ (X); 5.0µ (Yi) 0.04pm = 0.04pm -0.04pm = 0.376µ (Yi); 5.0µ (Yi) 0 = 0.370µ (Yi); 5.0µ (Yi) 0 = 0.370µ (Yi); 5.0µ (Yi) 0 = 0.372µ (Yi); 5.0µ (Yi) 0 = 0.372µ (Yi); 5.0µ (Yi) 0 = 0.372µ (Yi); 5.0µ (Yi) 0 = 0 5 10 1 = 0 5 30µ 367 1 = 0 5 30µ 367 1 = 0 5 30µ 37 3 = 0 5 500hrs 1 = 1000 2 50000 2 0000 = 1000 2 1000 2 0000 = 1000 2 1000 1000 = 1000 2 1000 2 1000 = 1000 2 68 7 1 Lovoling OFF 2 69 7 7 5 | | | | | 0.0169µ (Xr); 0.0208µ (Yr) | ð |
| Notice | | | Stepping Accuracy Wafer 3 | < 0.04µ 3sd | 0.0103µ (XI); 0.0114µ (YI) | ð |
| S ± 0.5pm -0.26pm (X); -0.31pm (Y) S ± 0.5pm -0.04ppm Bit -0.04ppm Altrass -0.0445 Bit -0.3'-0.5mm Altrass -0.045 Bit -0.0445 | | | | | 0.0151µ (Xr); 0.0232µ (Yr) | ð |
| $\leq \pm 0.5$ ptm -0.04 ppm $\leq 30\mu 3sd$ $\leq 30\mu 3sd$ $3.7\theta\mu (X)$ $\leq 30\mu 3sd$ $= 3.7\theta\mu (X)$ $= 3.7\theta\mu (X)$ $afer Per Pass$ $s 10$ $n = 0.045$ $afer Per Pass$ ≤ 10 $1 = 3.6 mm$ $afer Per Pass$ ≤ 10 $1 = 3.6 mm$ $afer Per Pass$ ≤ 10 $1 = 3.6 mm$ $afer Per Pass$ ≤ 10 0 $afer Per Pass$ ≤ 2500 0 $afer Per Pass$ $= 20000$ $= 20000$ $afer Per Pass$ $= 263\%$ $= 77.5$ $bosure \geq 68 77.5 bosure \geq 68 77.5 bosure \geq 68 77.5 bosure \geq 68 77.5 bosure 77.5 $ | | | Scaling | < ± 0.5ppm | -0.26ppm (X); -0.31ppm (Y | |
| ≤ 30µ 3sd ≤ 30µ 3sd 3.76µ (%) 0<6mm | | | Orthogonality | < ± 0.5ppm | -0.04ppm | - |
| T23µ (Y); 5.0µ (Y) 0 - 6mm 7.23µ (Y); 5.0µ (Y) afer Per Pass 5 10 1 - 3 - 6 mm afer Per Pass 5 10 1 and Develop Without 25 0 0 and Develop Without 2 0 0 anter 2 0 | 6. PRE-ALIGNMENT ACCURACY | 6a. | Mechanical Prealignment Accuracy | ≤ 30µ 3sd | 3.76µ (X) | ð |
| 0.6mm $1.3.6 \text{mm}$ $+0.3-0.5 \text{mm}$ $+0.0.0.445$ afer Per Pass ≤ 10 1 afer Per Pass ≤ 10 1 afer Per Pass ≤ 50 1 and Develop Without 25 0 and Develop Without 25 0 0 500 0 0 500 0 0 0 0 500 <td< td=""><td></td><td></td><td></td><td></td><td>7.23µ (YI); 5.0µ (Yr)</td><td>ð</td></td<> | | | | | 7.23µ (YI); 5.0µ (Yr) | ð |
| 40.3/-0.5mm $+0.3/-0.445$ afer Per Pass ≤ 10 1afer Per Pass ≤ 10 1and Develop Without ≤ 50 0and Develop Without 25 0and Develop Without 25 0 ≤ 25 00 ≤ 26 00 ≤ 200 $2500hrs$ 147hrs ($23/1/97$) $\leq 2hrs$ $2hrs$ 97.2 $\leq 2hrs$ 20000 20000 ist ≥ 20000 20000 ≥ 20000 20000 ≥ 20000 20000 ≥ 20000 20000 ≥ 68 71Levelling ON ≥ 68 71Levelling OFF ≥ 68 71Levelling OFF ≥ 68 71Levelling OFF ≥ 68 71initisation ≥ 68 71 | 7. OPTICAL EBR | | Edge Bead Removal Capability | 0 - 6mm | 1 - 3 - 6 mm | ð |
| afer Pease ≤ 10 1afer Per Pass ≤ 3 0 and Develop Without ≤ 5 0 and Develop Without 25 0 25 500 $147hs$ ($23/1/97$) 25 500 $147hs$ ($23/1/97$) 25 500 $147hs$ ($23/1/97$) 25 $2500hrs$ $147hs$ ($23/1/97$) 25 20000 0 250000 20000 71 20000 20000 20000 77.5 20000 71 20000 20000 20000 77.5 20000 77.5 20000 77.5 20000 77.5 20000 77.5 20000 77.5 20000 77.5 20000 77.5 20000 77.5 20000 77.5 < | | | Edge Bead Removal Accuracy | +0.3/-0.5mm | +0/-0.445 | ð |
| afer Perses \leq 30and Develop Without \geq 5 \geq 30and Develop Without \geq 5 \geq 50 \geq 500 \geq 500 \geq 500hs147hrs (23/197) \geq 500hs \geq 200hs147hrs (23/197) \geq 2000 \geq 20000 $=$ 20000ist \geq 20000 \geq 0000 \geq 20000 \geq 0000 \geq 20000 \geq 0000 \geq 20000 \geq 00000 \geq 20000 \geq 0000 \geq 20000 \geq 00000 \geq 1000 \geq 0000 \geq 20000 \geq 00000 \geq 0000 \geq 00000 \geq 20000 \geq 00000 | 8. CONTAMINATION | | Particles ≥ 0.3t Added Per 150mm Wafer Per Pass | < 10 | - | ð |
| and Develop Without 25 0 0 0 500 0 147hrs (23/1/97) 2 500hrs 147hrs (23/1/97) 2 2hrs 97.2 23/1/97) 2 20000 20000 0 2000 200 200 200 200 2000 200 200 2000 200 200 20000 200 200 | | | Particles 2 0.5µ Added Per 150mm Wafer Per Pass | × 3 | 0 | ¥ |
| 25 0 500 500 0 500 500hrs 147hrs (23/1/97) 2 2hrs 2 4hrs**** (23/1/97) 2 2hrs 97.2 2 2hrs 97.2 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 20000 2 20000 2 20000 2 20000 2 20000 2 20000 2 20000 2 20000 2 20000 2 20000 2 20000 2 2 20000 2 20000 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 | | + | Curled Mediate Through Cost Eveness and Davator Mithout | | | |
| 25 0 500 500 0 500 $147hs$ $(23/1/97)$ $\leq 2hrs$ $4hrs***$ $(23/1/97)$ $\leq 2hrs$ $4hrs***$ $(23/1/97)$ $\leq 2hrs$ 97.2 97.2 $\geq 93\%$ 97.2 97.2 ≥ 20000 20000 20000 20000 20000 20000 $\Delta 0000$ 20000 71 Levelling ON ≥ 68 71 Levelling OFF ≥ 69 77.5 | | | Error/Assist: | | | |
| 500 500 0 2 500hrs 147hrs (23/1/97) 2 2hrs 147hrs (23/1/97) 2 2hrs 4hrs*** (23/1/97) 2 2hrs 2 3% 2 2hrs 4hrs*** (23/1/97) 2 20000 2 37.2 2 20000 2 0000 2 1000 2 20000 2 20000 2 00000 2 20000 2 00000 2 20000 2 00000 2 20000 2 00000 2 20000 2 00000 2 20000 2 00000 2 20000 2 00000 2 68 7 1 2 69 77.5 Levelling OFF 2 69 77.5 Levelling OFF 2 69 77.5 Levelling OFF 2 69 77.5 | | | Tost () | 25 | 0 | ð |
| \geq 500hrs147hrs(23/1/97)stress2 2hrs(147)rrsstress2 2hrs(172) \geq 23%97.2 \geq 97.297.2 \geq 10001000 \geq 2000020000 \geq 20000200 | | | Test II) | 500 | 0 | ð |
| $\leq 2hrs$ $4hrs^{***}$ (23/1/97)ist $\geq 23\%$ 97.2 $\geq 83\%$ 97.2 ≥ 1000 ≥ 0000 ≥ 20000 20000 < | | | | ≥ 500hrs | 147hrs (23/1/97) | oK**** |
| \geq 83% \geq 97.2ist \geq 10001000 \geq 1000 \geq 20000 \geq | | | MTR | < 2hrs | 4hrs*** (23/1/97) | oK*** |
| ist $\gtrsim 1000$ 1000 ist $\gtrsim 1000$ 20000 Aultimark, 45 Shots Per ≥ 20000 20000 Aultimark, 45 Shots Per ≥ 20000 20000 Austrian ≥ 68 71 Levelling ON ≥ 68 71 Levelling OFF ≥ 69 77.5 Levelling OFF ≥ 69 77.5 udes qualification time. imisation | | | Guaranteed Uptime | > 93% | 97.2 | ð |
| $ \begin{tabular}{ c c c c c c c } \hline $\geq 20000 & $20000 & $20000 & $20000 & $20000 & $20000 & $20000 & $20000 & $20000 & $20000 & 71 & $200000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 & $20000 & 71 $ | | | Number Of Wafers Without Error/Assist | ≥ 1000 | 1000 | ð |
| Multimark, 45 Shots Per Abols Per 2005 Per 2005 Per 2005 Per 71 Levelling ON 2005 2000 2000 77.5 2000 77.5 2000 2000 2000 2000 2000 2000 2000 20 | | | Number Of Wafers Without Breakage | ≥ 20000 | 20000 | ð |
| posure ≥ 68 71 Levelling ON ≥ 69 77.5 Levelling OFF ≥ 69 77.5 Levelling OFF ≥ 69 77.5 | 10. THROUGHPUT | | 150mm Wafers Per Hour With AGA, Multimark, 45 Shots Per | | | |
| Leveling ON ≥ 68 71 Leveling OFF ≥ 69 77.5 Leveling OFF ≥ 69 77.5 udes qualification time. | | | Wafer, 20mmx20mm and 0.15secs Exposure | | | |
| Levelling OFF ≥ 69 77.5 udes qualification time. | | | Die By Die Levelling ON | ≥ 68 | 71 | ¥ |
| *** It is part of Canon's reponsibility to get this figure improved in the future. *** mttr is by definition the diagnose+fixing time (qualification excluded). Here it includes qualification time. ** all layers on stepper6,8 have Cpk>1; except C05 130 Cpk<1; matter of proces optimisation | | | Die By Die Levelling OFF | 59 ≥ | 77.5 | ¥ |
| *** mttr is by definition the diagnose+fixing time (qualification excluded). Here it includes qualification time. | **** It is part of Canon's reponsibilit | Ity to get the | is fl _u ure improved in the future. | | | |
| ** all layers on stepper6,8 have Cpk>1; except C05 130 Cpk<1; matter of proces optimisation | *** mttr is by definition the diagnosi | se+fixing tim | he (qualification excluded). Here it includes qualification time. | | | |
| | ** all layers on stepper6,8 have Cp | ok>1; except | t C05 130 Cpk<1; matter of proces optimisation | | | |